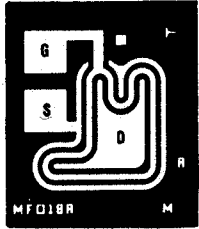


CHIP NUMBER

FMN1.2



.023"
(0.584mm)

.021"
(0.533mm)

Die Size: 21 x 23 (mils)
0.533 x 0.584(mm)
Pad Size 4 x 4 (mils)
BODY-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000 Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

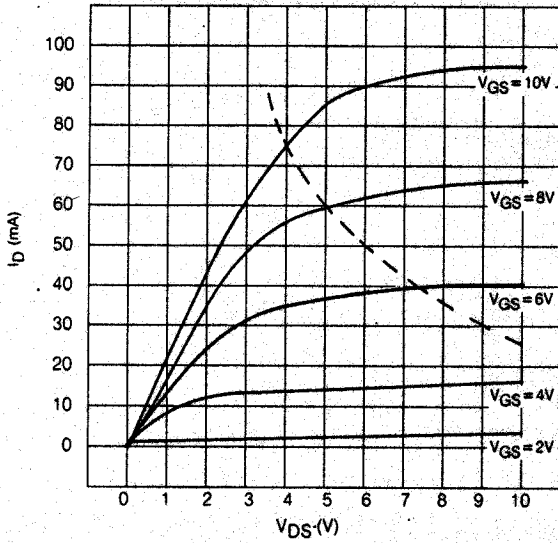
It is advisable that:

- a) the die be eutectically mounted with gold silicon preform 98/2%.
- b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

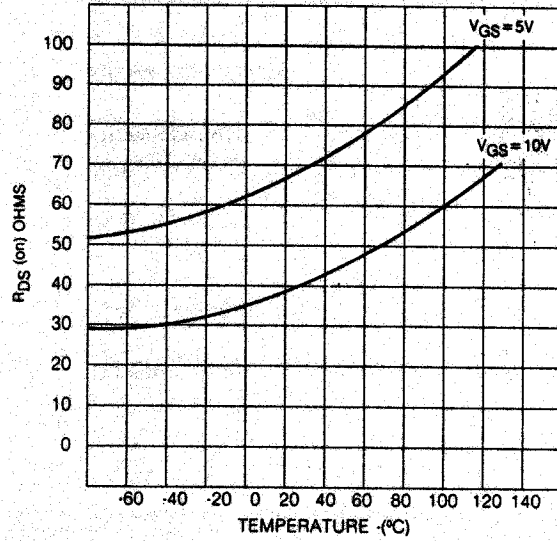
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVDSS	20	33		V	$I_D = 1.0\mu A, V_{GS} = 0, V_{BS} = 0$
IDSS		.01	10	nA	$V_{DS} = 10V, V_{GS} = 0, V_{BS} = 0$
IGSS		0.2	5	pA	$V_{GB} = \pm 25V, V_{DB} = V_{SB} = 0$
VTH	0.1	1.0	2.5	V	$V_{DS} = V_{GS} = V_{TH}, I_D = 1\mu A$
gfs	8.0	10		ms	$V_{DS} = 10V, I_D = 20mA, f = 1KHz$
RDS		70	100	Ω	$I_{DS} = 0.1mA, V_{GS} = 5.0V$
Ciss			4.5	pF	$V_{DS} = 15V, I_D = 20mA, f = 1MHz$
Coss			1.3	pF	$V_{DS} = 15V, I_D = 20mA, f = 1MHz$
Crss			1.2	pF	$V_{DS} = 15V, I_D = 20mA, f = 1MHz$

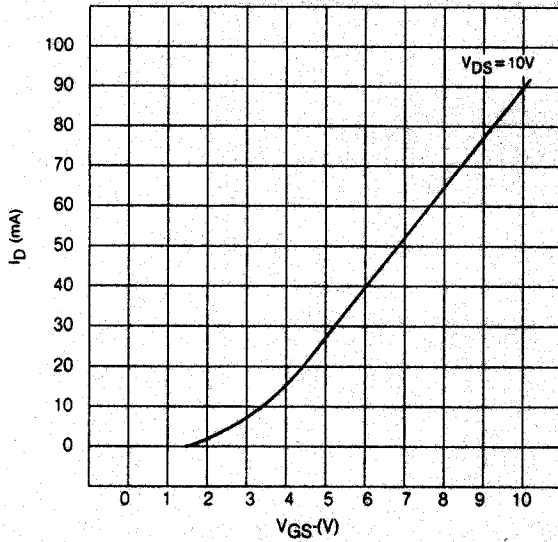
DRAIN CURRENT VS
DRAIN-TO-SOURCE VOLTAGE



DRAIN-TO-SOURCE RESISTANCE
VS TEMPERATURE



DRAIN CURRENT VS
GATE-TO-SOURCE VOLTAGE



TRANSCONDUCTANCE VS
GATE-TO-SOURCE VOLTAGE

